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Kim et al.

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(54) **FAN-OUT SEMICONDUCTOR PACKAGE**

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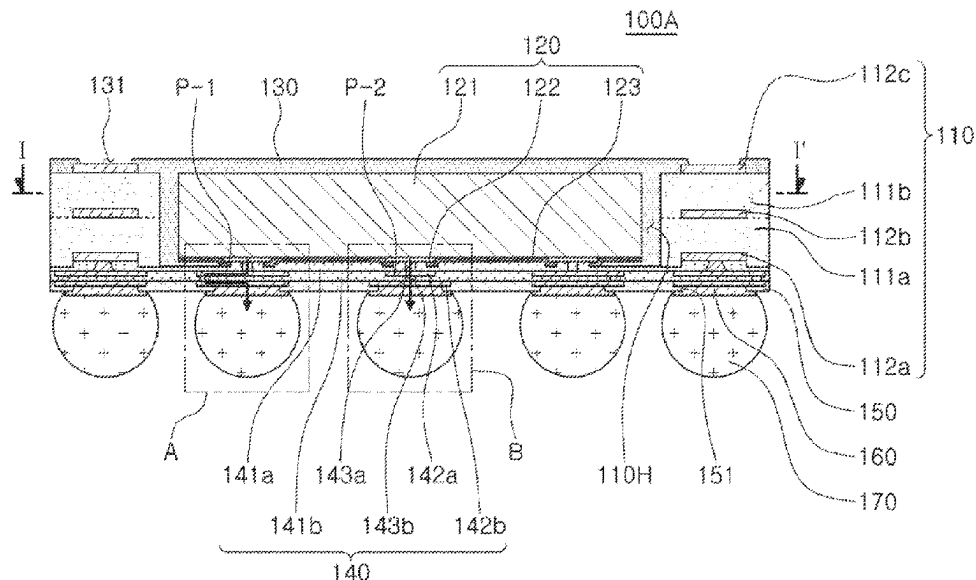
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(57) **ABSTRACT**

A fan-out semiconductor package includes connection pads of a semiconductor chip that are redistributed and electrically connected to connection terminals by an interconnection member. In the fan-out semiconductor package, disposition forms of vias and pads in the interconnection member are designed so that stress may be reduced, such that reliability is improved.

17 Claims, 14 Drawing Sheets



Related U.S. Application Data

continuation of application No. 16/787,758, filed on Feb. 11, 2020, now Pat. No. 11,094,623, which is a continuation of application No. 15/457,260, filed on Mar. 13, 2017, now Pat. No. 10,580,728.

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(52) **U.S. Cl.**

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 (2013.01); **H01L 2924/1431** (2013.01); **H01L**
2924/1433 (2013.01); **H01L 2924/3511**
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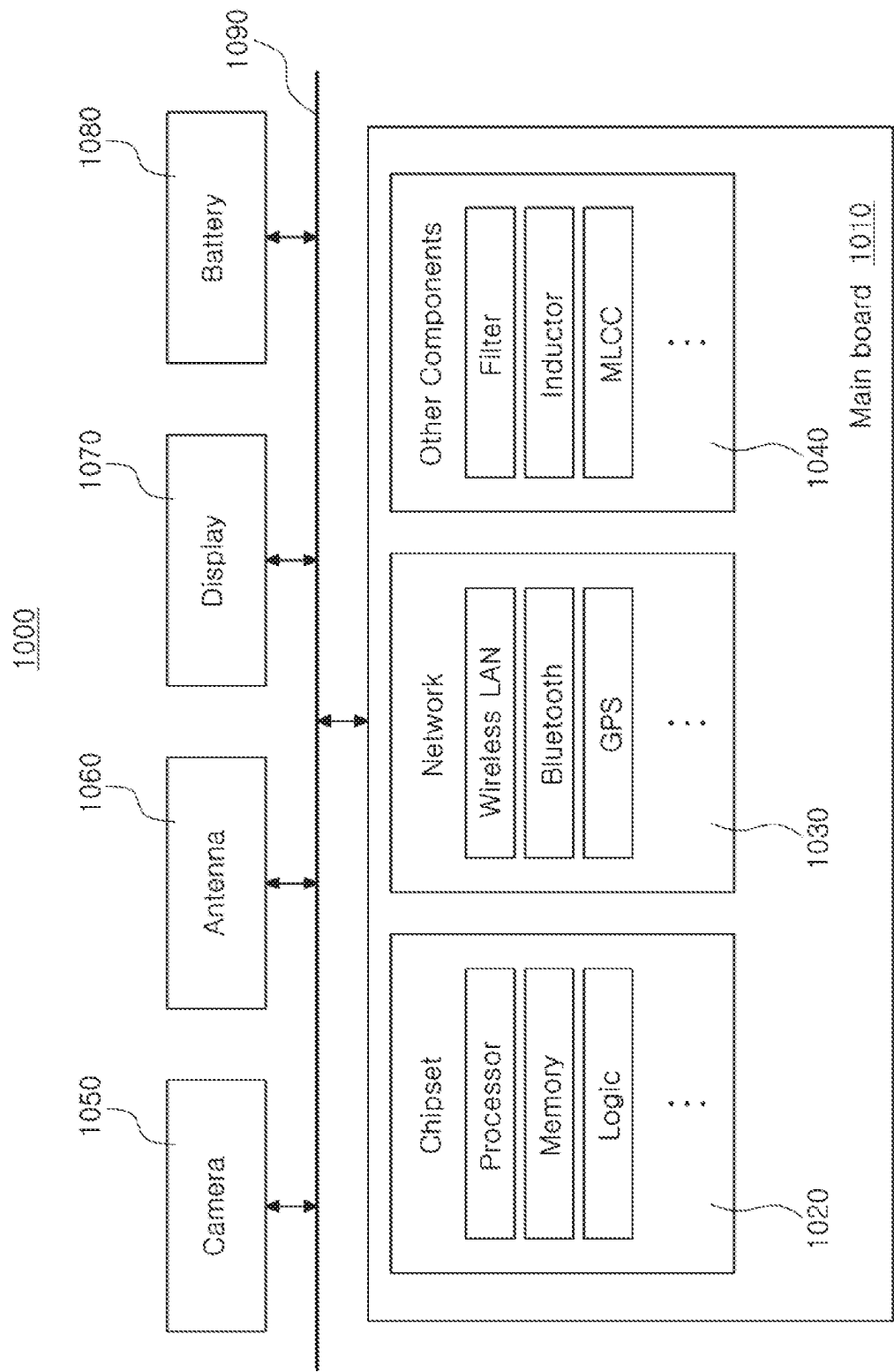
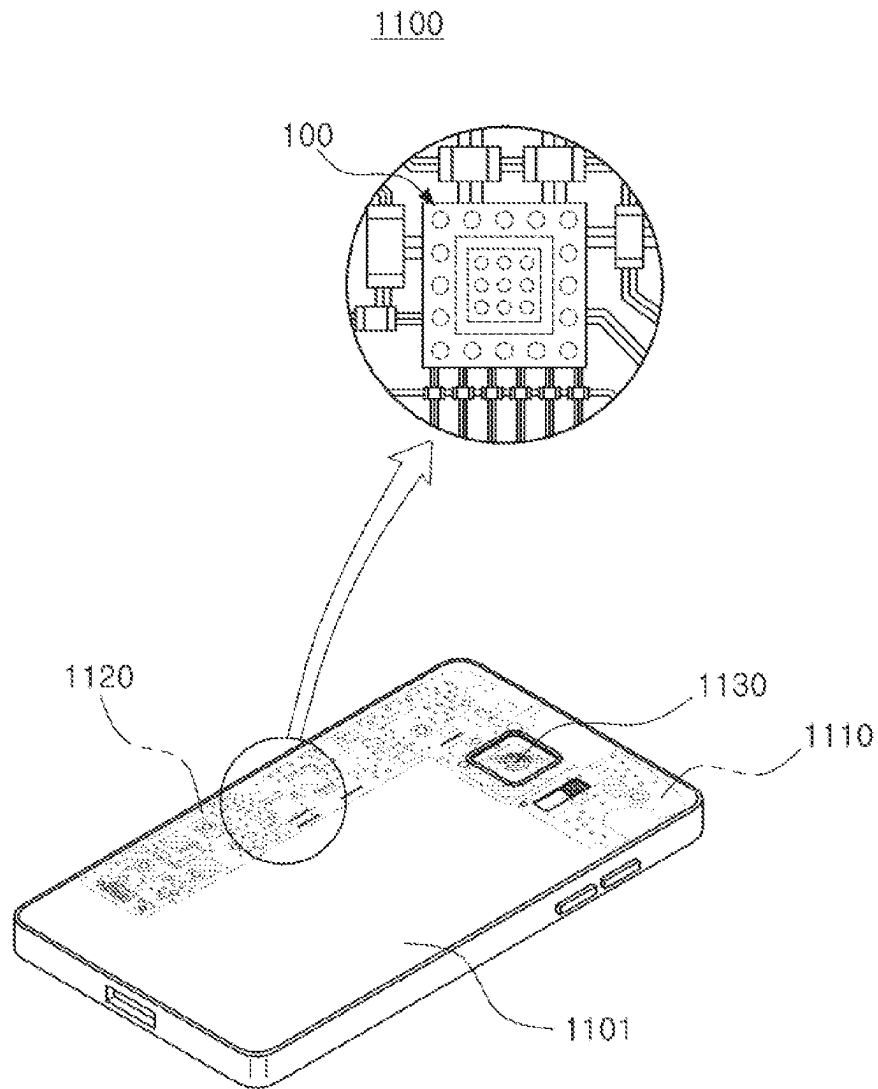


FIG. 1



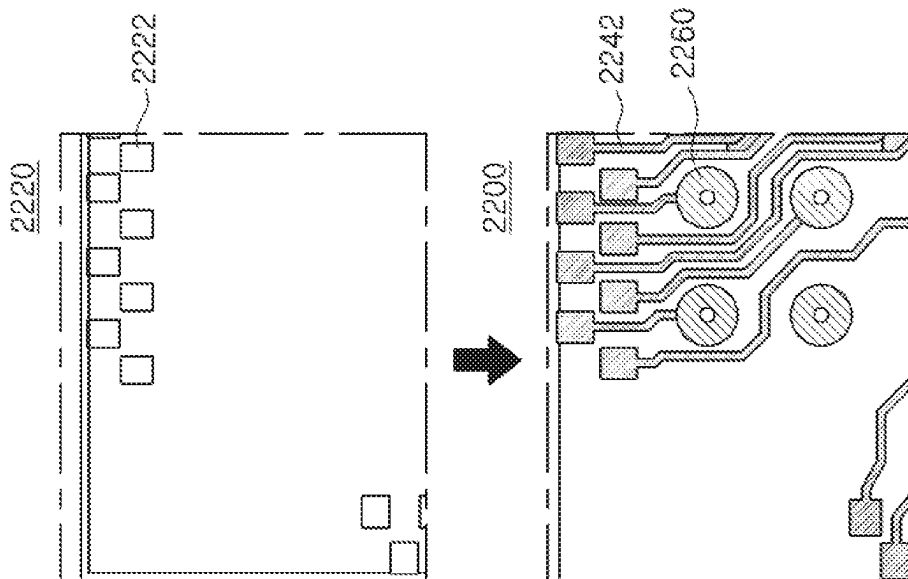


FIG. 3B

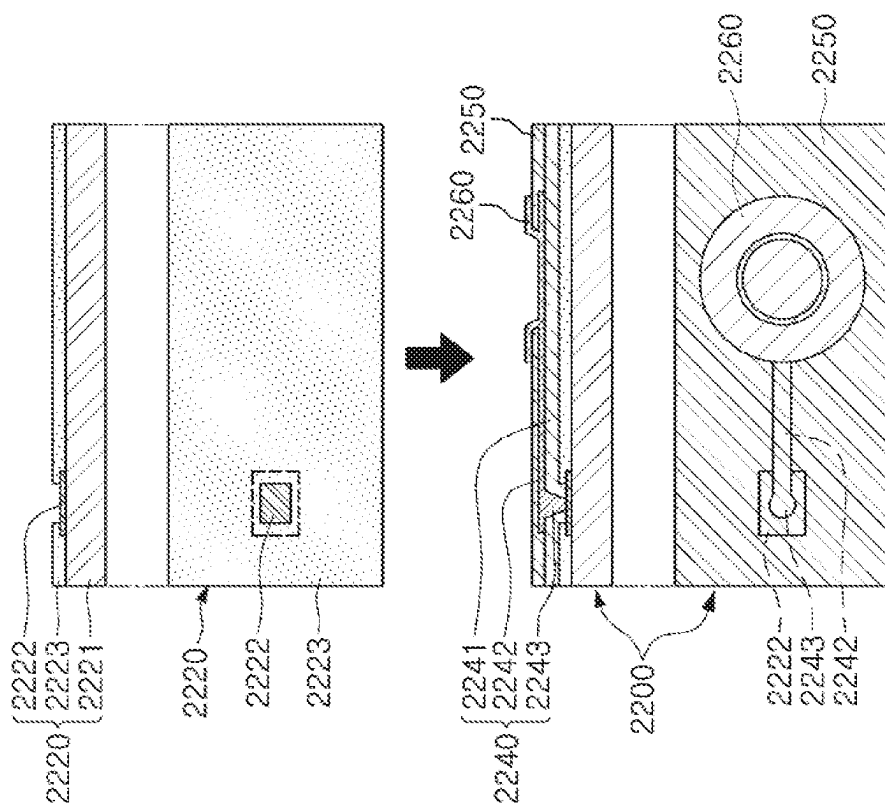


FIG. 3A

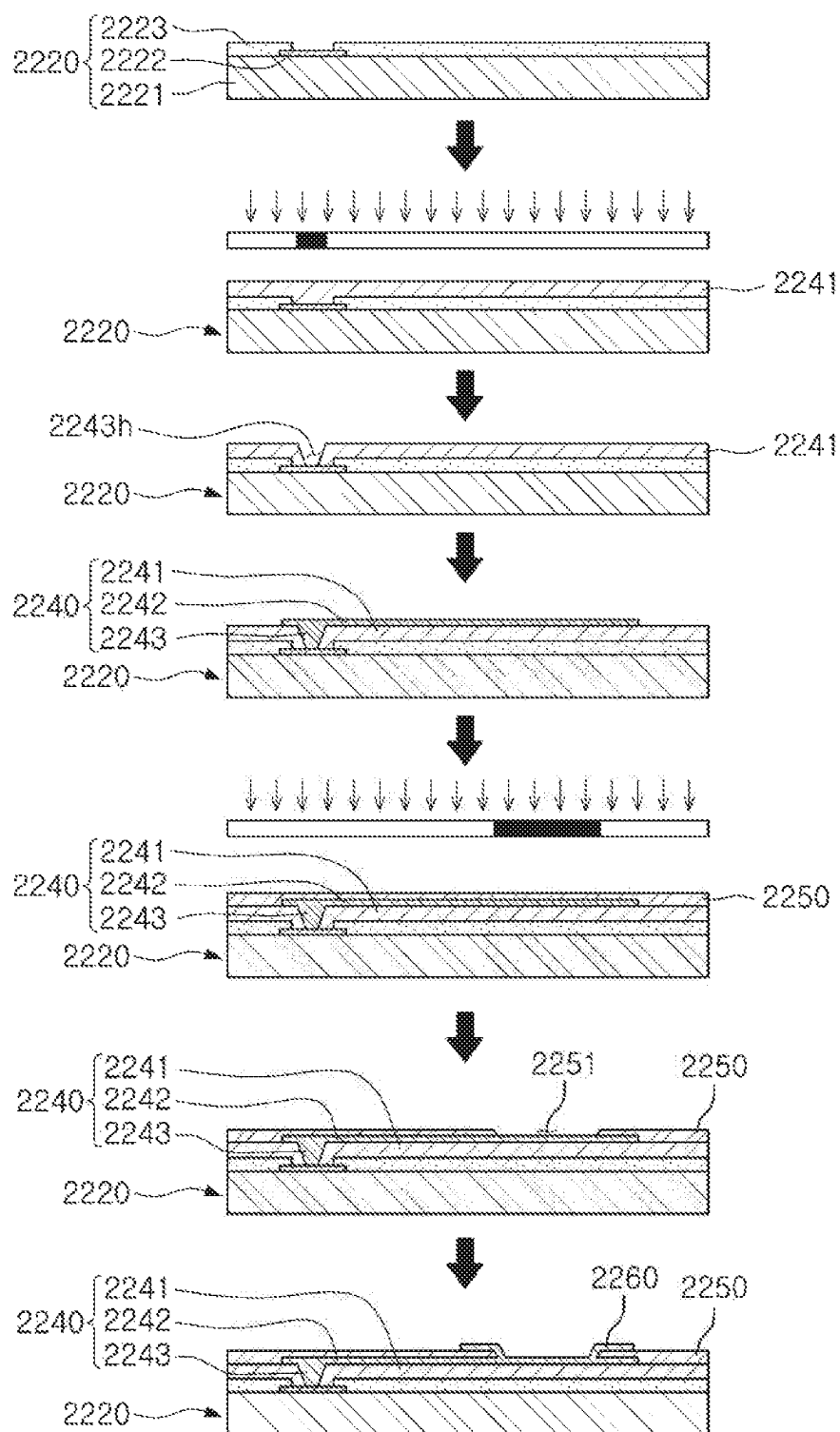


FIG. 4

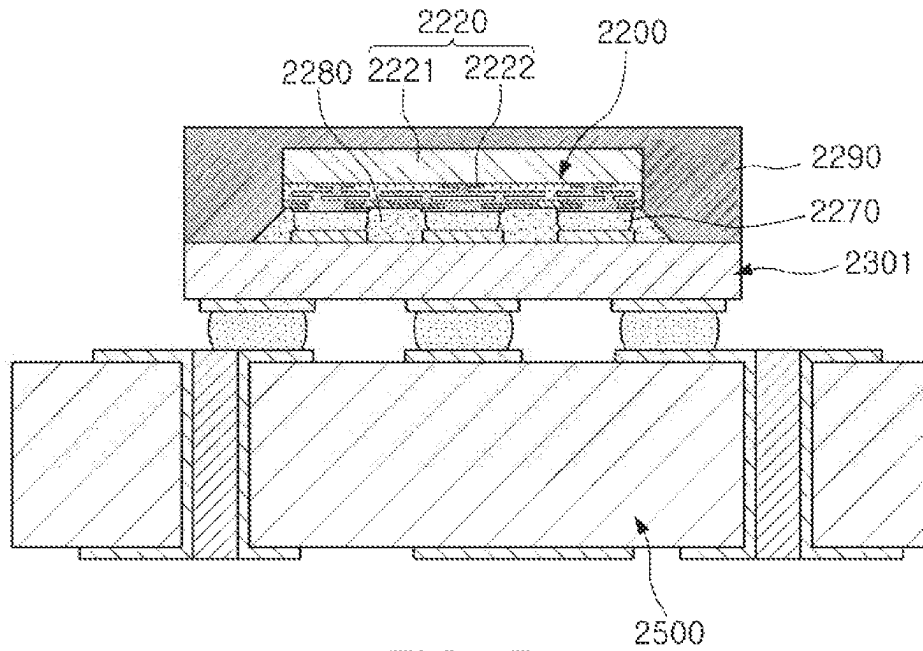


FIG. 5

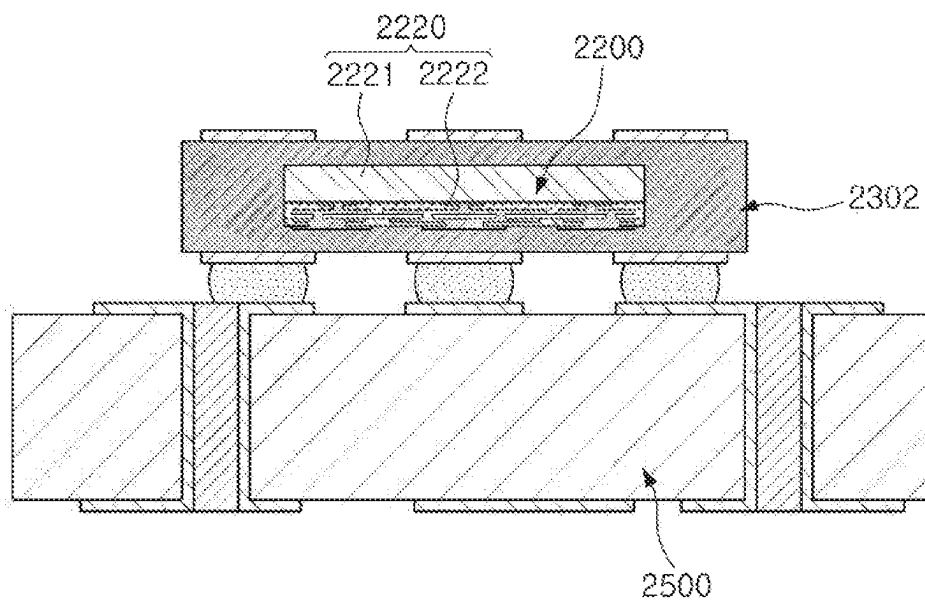


FIG. 6

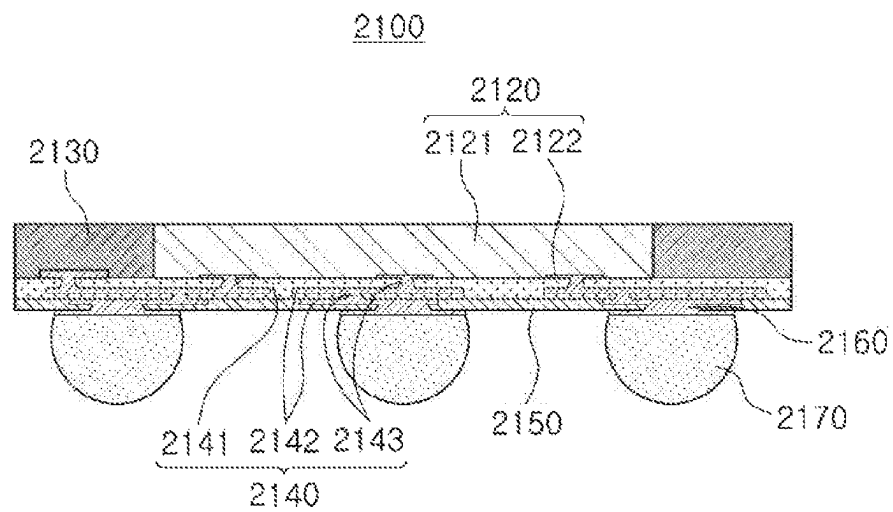


FIG. 7

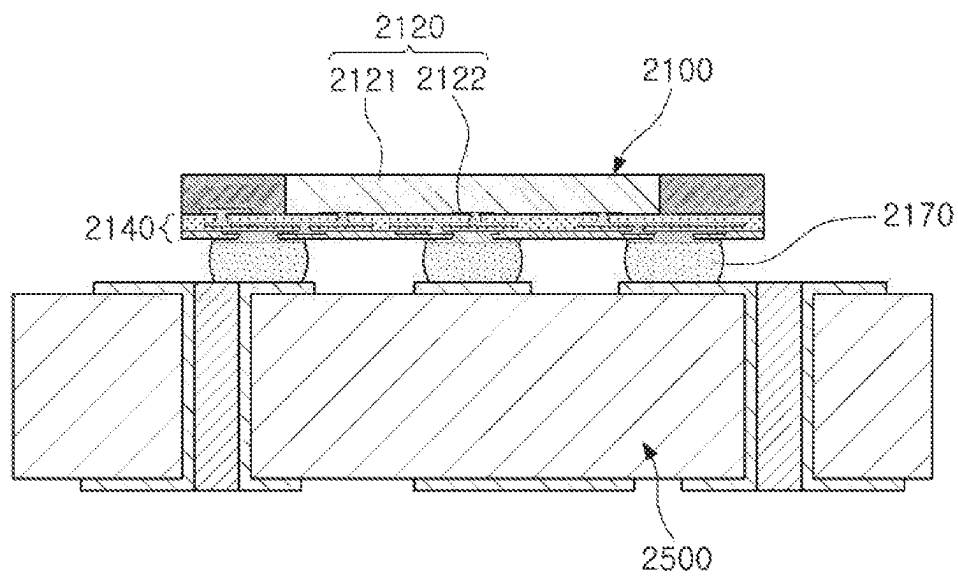
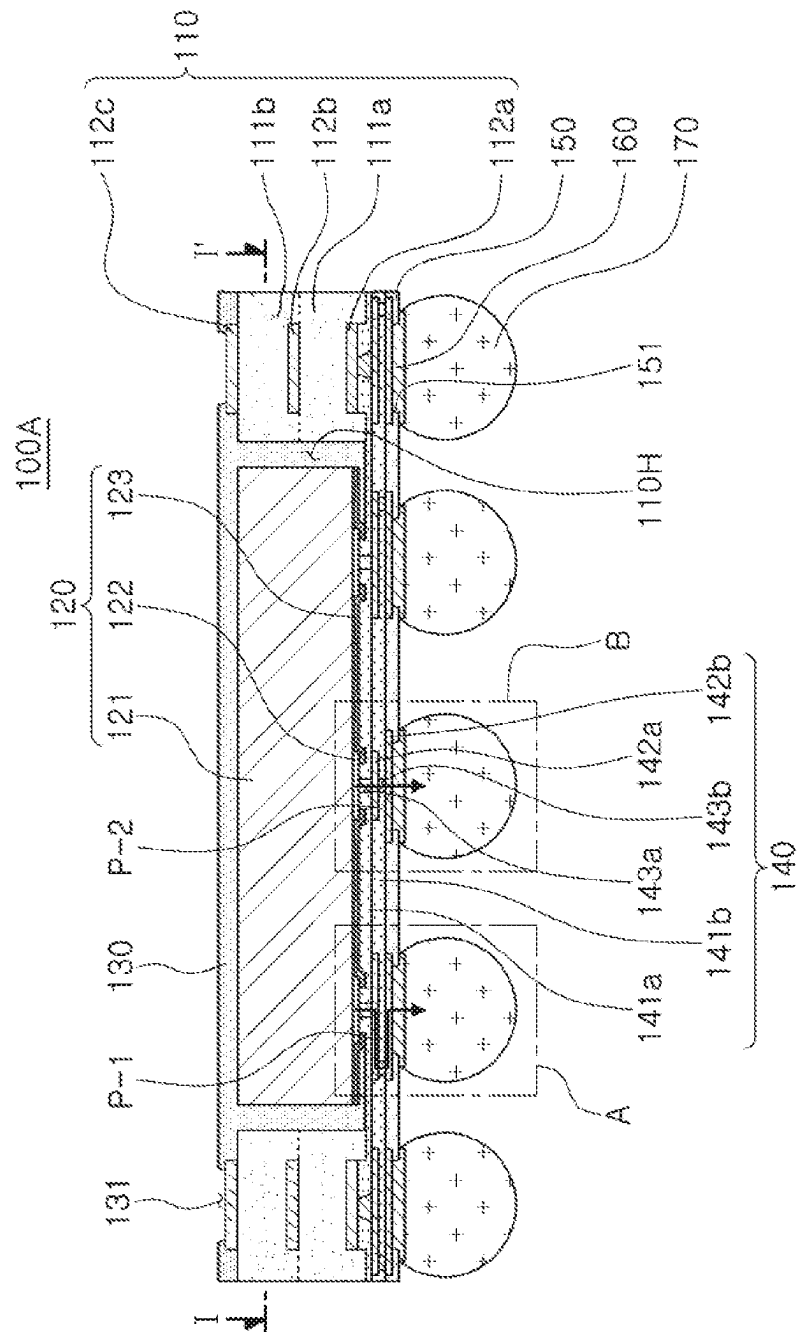


FIG. 8















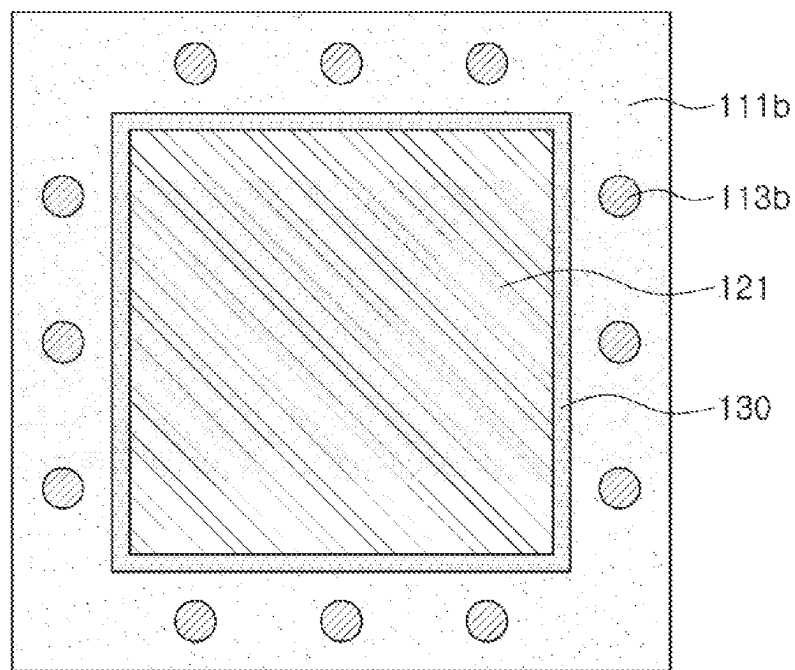






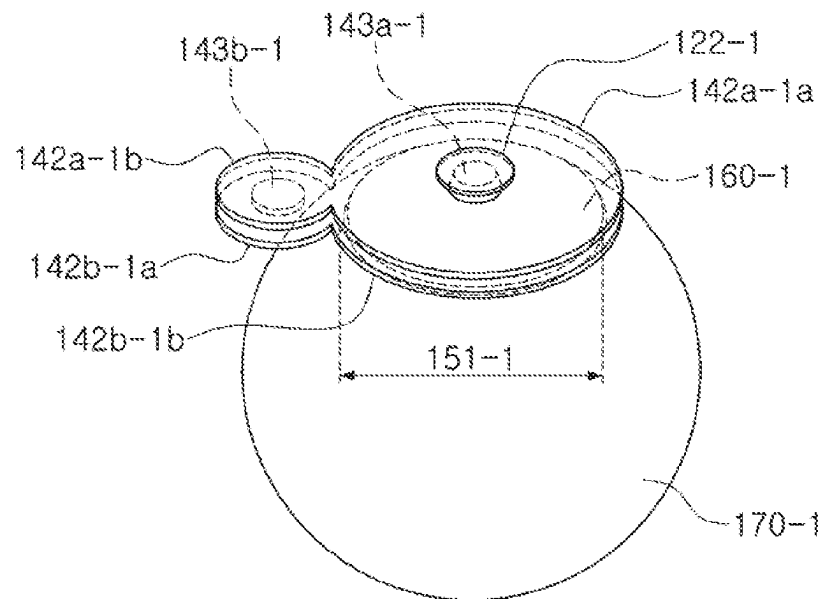




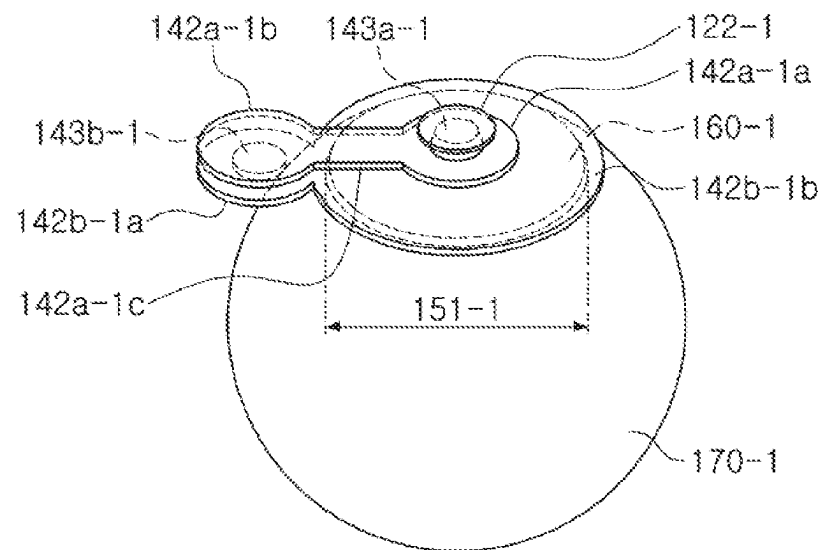
I-I'

FIG. 10



A

FIG. 11A



A

FIG. 11B

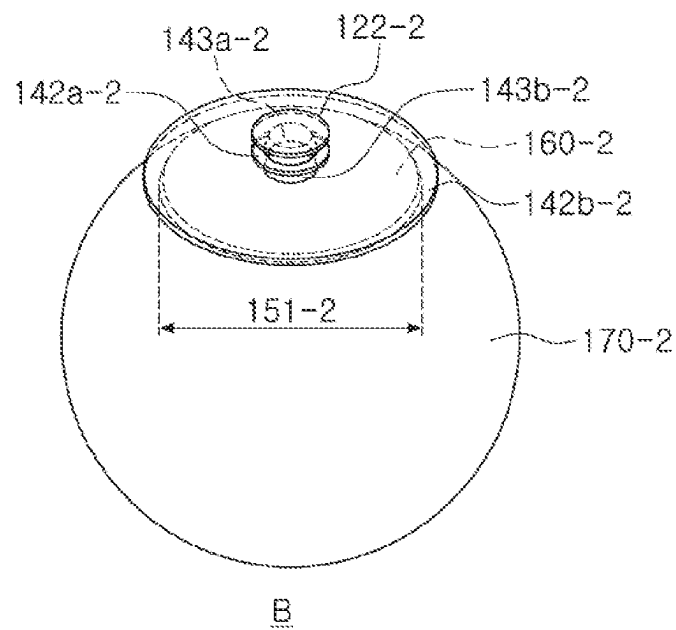


FIG. 12

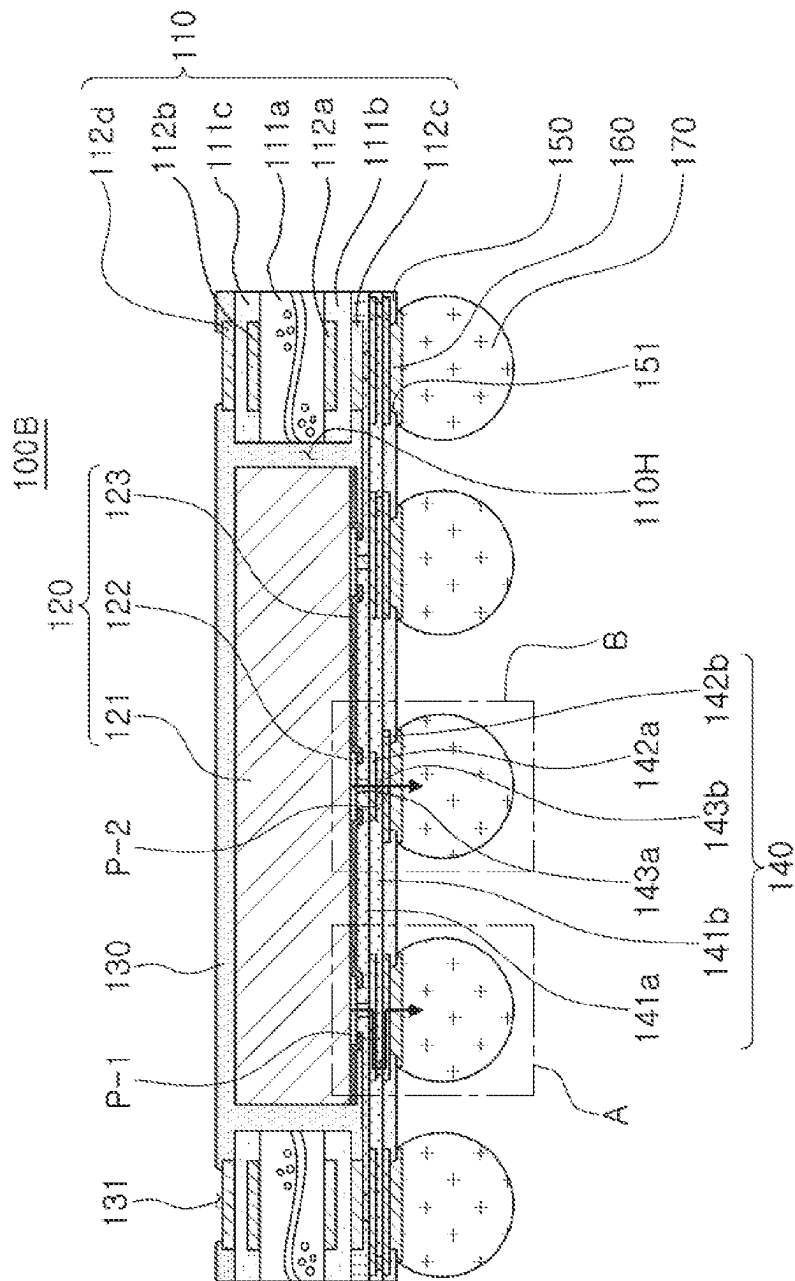


FIG. 13

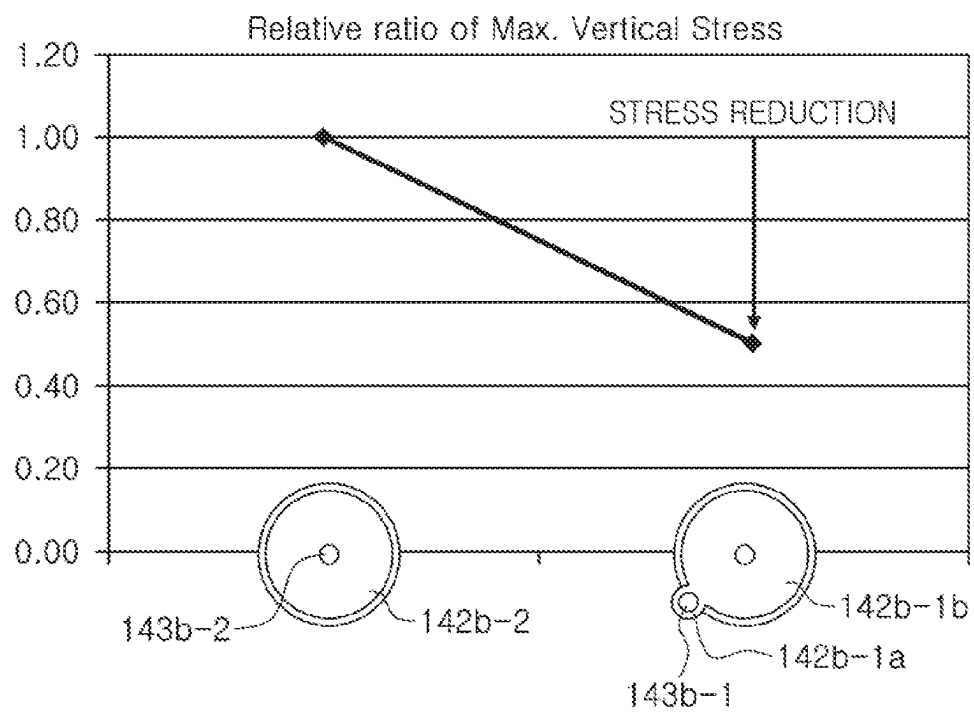


FIG. 14

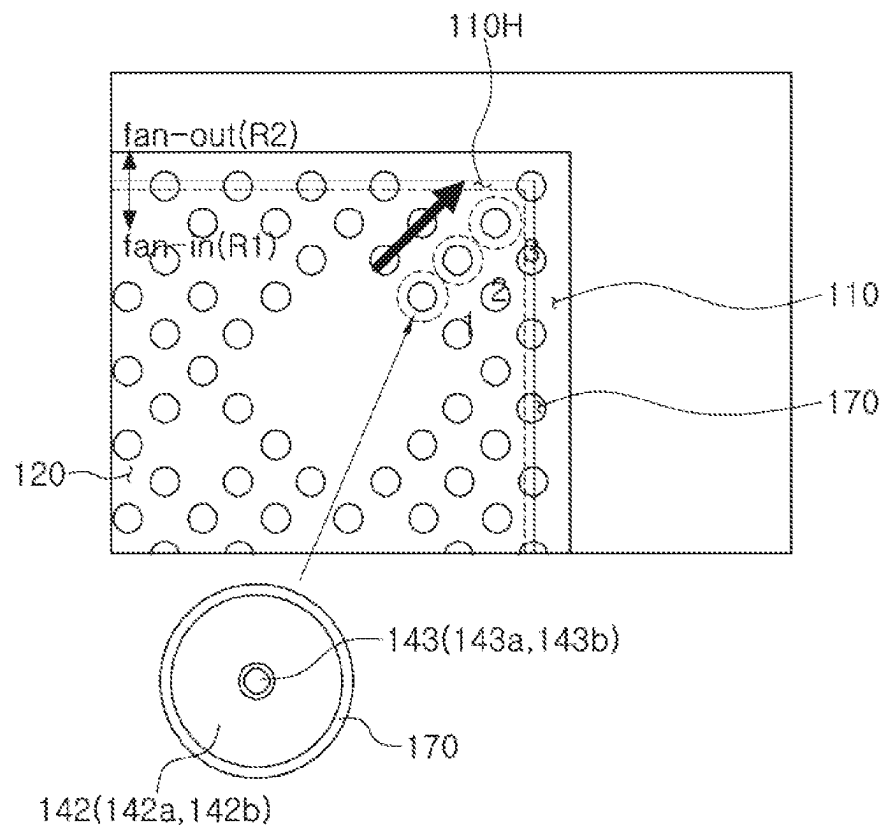


FIG. 15A

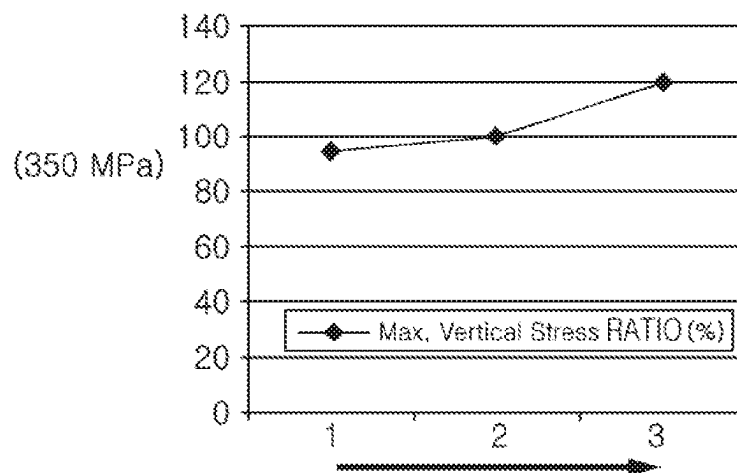


FIG. 15B

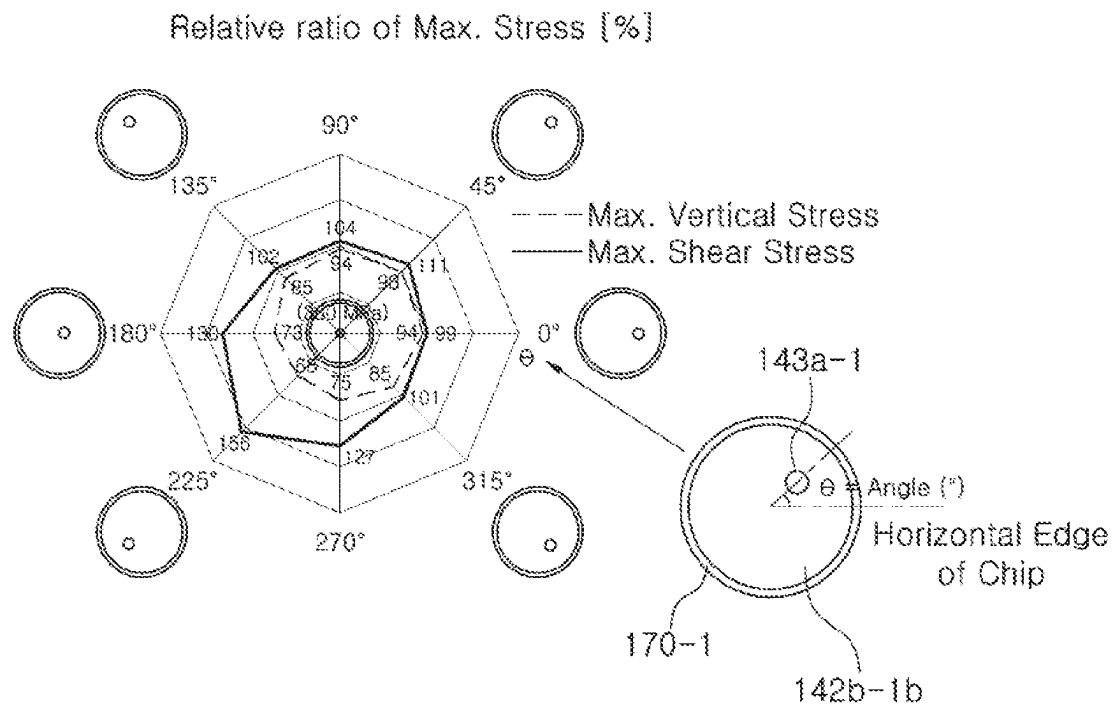


FIG. 16

FAN-OUT SEMICONDUCTOR PACKAGE**CROSS-REFERENCE TO RELATED APPLICATIONS**

This application is a continuation of U.S. application Ser. No. 17/401,376, filed on Aug. 13, 2021, which is a continuation of U.S. application Ser. No. 16/787,758, filed on Feb. 11, 2020, now U.S. Pat. No. 11,094,623, issued on Aug. 17, 2021, which is a continuation of U.S. application Ser. No. 15/457,260, filed on Mar. 13, 2017, now U.S. Pat. No. 10,580,728, issued on Mar. 3, 2020, which claims priority from Korean Patent Application Nos. 10-2016-0094614 filed on Jul. 26, 2016 and 10-2016-0078874 filed on Jun. 23, 2016 in the Korean Intellectual Property Office, the entire disclosures of which are incorporated herein by reference.

BACKGROUND

1. Field

The present disclosure relates to a semiconductor package, and more particularly, to a fan-out semiconductor package in which connection terminals may extend outwardly of a region in which a semiconductor chip is disposed.

2. Description of Related Art

A significant recent trend in the development of technology related to semiconductor chips has been to reduce the size of semiconductor chips. Therefore, in the case of package technology, in accordance with a rapid increase in demand for small-sized semiconductor chips, or the like, the implementation of a semiconductor package having a compact size while including a plurality of pins has been demanded.

One type of package technology suggested to satisfy the technical demand described above is a fan-out package. Such a fan-out package has a compact size and may allow a plurality of pins to be implemented by redistributing connection terminals outwardly of a region in which a semiconductor chip is disposed.

SUMMARY

An aspect of the present disclosure may provide a fan-out semiconductor package in which reliability of a via may be improved.

One of several solutions suggested through the present disclosure is to dispose vias and pads in an interconnection member redistributing connection pads of a semiconductor chip and connecting the connection pads of the semiconductor chip to connection terminals so that stress may be reduced.

According to an aspect of the present disclosure, a fan-out semiconductor package may include: a first interconnection member having a through-hole; a semiconductor chip disposed in the through-hole of the first interconnection member and having an active surface having a connection pad disposed thereon and an inactive surface opposing the active surface; an encapsulant encapsulating at least portions of the first interconnection member and the inactive surface of the semiconductor chip; a second interconnection member disposed on the first interconnection member and the active surface of the semiconductor chip; and a connection terminal disposed on the second interconnection member. The

first interconnection member and the second interconnection member respectively include redistribution layers electrically connected to the connection pads of the semiconductor chip, and a connection pad and a connection terminal are electrically connected to each other by an electrical pathway in the second interconnection member, the electrical pathway including a first via connected to the connection pad and having a central axis disposed in an inner region of a connection terminal pad connected to the connection terminal and a second via connected to a via pad formed on the layer on which the connection terminal pad is disposed and having a central axis disposed in an outer region of the connection terminal pad.

BRIEF DESCRIPTION OF DRAWINGS

The above and other aspects, features, and advantages of the present disclosure will be more clearly understood from the following detailed description taken in conjunction with the accompanying drawings, in which:

FIG. 1 is a schematic block diagram illustrating an example of an electronic device system;

FIG. 2 is a schematic perspective view illustrating an example of an electronic device;

FIGS. 3A and 3B are schematic cross-sectional views illustrating states of a fan-in semiconductor package before and after being packaged;

FIG. 4 is schematic cross-sectional views illustrating a packaging process of a fan-in semiconductor package;

FIG. 5 is a schematic cross-sectional view illustrating a case in which a fan-in semiconductor package is mounted on an interposer substrate and is ultimately mounted on a main board of an electronic device;

FIG. 6 is a schematic cross-sectional view illustrating a case in which a fan-in semiconductor package is embedded in an interposer substrate and is ultimately mounted on a main board of an electronic device;

FIG. 7 is a schematic cross-sectional view illustrating a fan-out semiconductor package;

FIG. 8 is a schematic cross-sectional view illustrating a case in which a fan-out semiconductor package is mounted on a main board of an electronic device;

FIG. 9 is a schematic cross-sectional view illustrating an example of a fan-out semiconductor package;

FIG. 10 is a schematic plan view taken along line I-I' of the fan-out semiconductor package of FIG. 9;

FIG. 11A is a schematic enlarged view according to an example of A of the fan-out semiconductor package of FIG. 9;

FIG. 11B is a schematic enlarged view according to another example of A of the fan-out semiconductor package of FIG. 9;

FIG. 12 is a schematic enlarged view according to an example of B of the fan-out semiconductor package of FIG. 9;

FIG. 13 is a schematic cross-sectional view illustrating another example of a fan-out semiconductor package;

FIG. 14 is a schematic view illustrating a stress reducing effect in a case in which a central axis of a via is disposed in an outer region of a connection terminal pad or an opening;

FIGS. 15A and 15B are schematic views illustrating relative magnitudes of stress applied to vias at positions within a fan-out semiconductor package; and

FIG. 16 is a schematic view illustrating stress depending on a distance between a central axis of a via connected to a

connection pad of a semiconductor chip and a central axis of a connection terminal pad or an opening.

DETAILED DESCRIPTION

Hereinafter, exemplary embodiments in the present disclosure will be described with reference to the accompanying drawings. In the accompanying drawings, shapes, sizes, and the like, of components may be exaggerated or omitted for clarity.

The term “an exemplary embodiment” used herein does not refer to the same exemplary embodiment, and is provided to emphasize a particular feature or characteristic different from that of another exemplary embodiment. However, exemplary embodiments provided herein are considered to be able to be implemented by being combined in whole or in part one with another. For example, one element described in a particular exemplary embodiment, even if it is not described in another exemplary embodiment, may be understood as a description related to another exemplary embodiment, unless an opposite or contradictory description is provided therein.

The meaning of a “connection” of a component to another component in the description includes an indirect connection through a third component as well as a direct connection between two components. In addition, “electrically connected” means the concept including a physical connection and a physical disconnection. It can be understood that when an element is referred to with “first” and “second”, the element is not limited thereby. They may be used only for a purpose of distinguishing the element from the other elements, and may not limit the sequence or importance of the elements. In some cases, a first element may be referred to as a second element without departing from the scope of the claims set forth herein. Similarly, a second element may also be referred to as a first element.

Herein, an upper portion, a lower portion, an upper side, a lower side, an upper surface, a lower surface, and the like, are as depicted in the attached drawings. For example, a first interconnection member is disposed at a level above a second interconnection member. However, the claims are not limited thereto. In the present disclosure, a vertical direction refers to the abovementioned upward and downward directions, and a horizontal direction refers to a direction perpendicular to the abovementioned upward and downward directions. In this case, a vertical cross section refers to a case taken along a plane in the vertical direction, and an example thereof may be a cross-sectional view illustrated in the drawings. In addition, a horizontal cross section refers to a case taken along a plane in the horizontal direction, and an example thereof may be a plan view illustrated in the drawings.

Terms used herein are used only in order to describe an exemplary embodiment rather than limiting the present disclosure. In this case, singular forms include plural forms unless interpreted otherwise in context.

Electronic Device

FIG. 1 is a schematic block diagram illustrating an example of an electronic device system.

Referring to FIG. 1, an electronic device **1000** may accommodate a mother board **1010** therein. The mother board **1010** may include chip-related components **1020**, network-related components **1030**, other components **1040**, and the like, physically or electrically connected thereto. These components may be connected to others to be described below to form various signal lines **1090**.

The chip-related components **1020** may include a memory chip such as a volatile memory (for example, a dynamic random access memory (DRAM)), a non-volatile memory (for example, a read only memory (ROM)), a flash memory, or the like; an application processor chip such as a central processor (for example, a central processing unit (CPU)), a graphics processor (for example, a graphics processing unit (GPU)), a digital signal processor, a cryptographic processor, a microprocessor, a microcontroller, or the like; and a logic chip such as an analog-to-digital (ADC) converter, an application-specific integrated circuit (ASIC), or the like. However, the chip-related components **1020** are not limited thereto, and may also include other types of chip-related components. In addition, the chip-related components **1020** may be combined with each other.

The network-related components **1030** may be compatible with protocols such as wireless fidelity (Wi-Fi) (Institute of Electrical And Electronics Engineers (IEEE) 802.11 family, or the like), worldwide interoperability for microwave access (WiMAX) (IEEE 802.16 family, or the like), IEEE 802.20, long term evolution (LTE), evolution data only (Ev-DO), high speed packet access+ (HSPA+), high speed downlink packet access+ (HSDPA+), high speed uplink packet access+ (HSUPA+), enhanced data GSM environment (EDGE), global system for mobile communications (GSM), global positioning system (GPS), general packet radio service (GPRS), code division multiple access (CDMA), time division multiple access (TDMA), digital enhanced cordless telecommunications (DECT), Bluetooth, 3G, 4G, and 5G protocols, and any other wireless and wired protocols designated after the abovementioned protocols. However, the network-related components **1030** are not limited thereto, and may also include a variety of other wireless or wired standards or protocols. In addition, the network-related components **1030** may be combined with each other, together with the chip-related components **1020** described above.

Other components **1040** may include a high frequency inductor, a ferrite inductor, a power inductor, ferrite beads, a low temperature co-fired ceramic (LTCC), an electromagnetic interference (EMI) filter, a multilayer ceramic capacitor (MLCC), or the like. However, other components **1040** are not limited thereto, and may also include passive components used for various other purposes, or the like. In addition, other components **1040** may be combined with each other, together with the chip-related components **1020** or the network-related components **1030** described above.

Depending on a type of the electronic device **1000**, the electronic device **1000** may include other components that may or may not be physically or electrically connected to the mother board **1010**. These other components may include, for example, a camera module **1050**, an antenna **1060**, a display device **1070**, a battery **1080**, an audio codec, a video codec, a power amplifier, a compass, an accelerometer, a gyroscope, a speaker, a mass storage unit (for example, a hard disk drive), a compact disk (CD) drive, a digital versatile disk (DVD) drive, or the like. However, these other components are not limited thereto, and may also include other components used for various purposes depending on type of electronic device **1000**, or the like.

The electronic device **1000** may be a smartphone, a personal digital assistant (PDA), a digital video camera, a digital still camera, a network system, a computer, a monitor, a tablet PC, a laptop PC, a netbook PC, a television, a video game machine, a smartwatch, an automotive component, or the like.

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However, the electronic device **1000** is not limited thereto, and may be any other electronic device processing data.

FIG. **2** is a schematic perspective view illustrating an example of an electronic device.

Referring to FIG. **2**, a semiconductor package may be used for various purposes in the various electronic devices **1000** as described above. For example, a main board **1110** may be accommodated in a body **1101** of a smartphone **1100**, and various electronic components **1120** may be physically or electrically connected to the main board **1110**. In addition, other components that may or may not be physically or electrically connected to the main board **1110**, such as the camera module **1130**, may be accommodated in the body **1101**. Some of the electronic components **1120** may be the chip-related components, and the semiconductor package **100** may be, for example, an application processor among the chip-related components, but is not limited thereto. The electronic device is not necessarily limited to the smartphone **1100**, but may be other electronic devices as described above.

Semiconductor Package

Generally, numerous fine electrical circuits are integrated in a semiconductor chip. However, the semiconductor chip may not serve as a finished semiconductor product itself, and may be damaged due to external physical or chemical impacts. Therefore, the semiconductor chip itself may not be used, but may be packaged and used in an electronic device, or the like, in a packaged state.

Here, semiconductor packaging is required due to the existence of a difference in circuit widths between the semiconductor chip and a main board of the electronic device in terms of electrical connections. In detail, a size of connection pads of the semiconductor chip and intervals between the connection pads of the semiconductor chip are very fine, while sizes of component mounting pads of the main board used in the electronic device and intervals between the component mounting pads of the main board are significantly larger than those of the semiconductor chip. Therefore, it may be difficult to directly mount the semiconductor chip on the main board, and packaging technology for buffering a difference in circuit widths between the semiconductor chip and the main board is required.

A semiconductor package manufactured by the packaging technology may be classified as a fan-in semiconductor package or a fan-out semiconductor package depending on a structure and a purpose thereof.

The fan-in semiconductor package and the fan-out semiconductor package will hereinafter be described in more detail with reference to the drawings.

Fan-In Semiconductor Package

FIGS. **3A** and **3B** are schematic cross-sectional views illustrating states of a fan-in semiconductor package before and after being packaged.

FIG. **4** is schematic cross-sectional views illustrating a packaging process of a fan-in semiconductor package.

Referring to the drawings, a semiconductor chip **2220** may be, for example, an integrated circuit (IC) in a bare state, including a body **2221** including silicon (Si), germanium (Ge), gallium arsenide (GaAs), or the like, connection pads **2222** formed on one surface of the body **2221** and including a conductive material such as aluminum (Al), or the like, and a passivation layer **2223** such as an oxide film, a nitride film, or the like, formed on one surface of the body **2221** and covering at least portions of the connection pads **2222**. In this case, since the connection pads **2222** are significantly small, it is difficult to mount the integrated

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circuit (IC) on an intermediate level printed circuit board (PCB) as well as on the main board of the electronic device, or the like.

Therefore, an interconnection member **2240** may be formed on the semiconductor chip **2220** depending on a size thereof in order to redistribute the connection pads **2222**. The interconnection member **2240** may be formed by forming an insulating layer **2241** on the semiconductor chip **2220** using an insulating material such as photoimageable dielectric (PID) resin, forming via holes **2243** opening the connection pads **2222**, and then forming wiring patterns **2242** and vias **2243**. Then, a passivation layer **2250** protecting the interconnection member **2240** may be formed, an opening **2251** may be formed, and an under-bump metal layer **2260**, or the like, may be formed. That is, a fan-in semiconductor package **2200** including, for example, the semiconductor chip **2220**, the interconnection member **2240**, the passivation layer **2250**, and the under-bump metal layer **2260** may be manufactured through a series of processes.

As described above, the fan-in semiconductor package may have a package form in which all of the connection pads, for example, input/output (I/O) terminals, of the semiconductor chip are disposed inside the semiconductor chip, may have excellent electrical characteristics and may be produced at a low cost. Therefore, many elements mounted in smartphones have been manufactured in fan-in semiconductor package form. In detail, many elements mounted in smartphones have been developed to allow rapid signal transfer to be implemented while having a compact size.

However, since all I/O terminals need to be disposed inside the semiconductor chip in the fan-in semiconductor package, the fan-in semiconductor package has a large spatial limitation. Therefore, it is difficult to apply this structure to a semiconductor chip having a large number of I/O terminals or a semiconductor chip having a compact size. In addition, due to the disadvantage described above, the fan-in semiconductor package may not be directly mounted and used on the main board of the electronic device. Here, even though a size of the I/O terminals of the semiconductor chip and an interval between the I/O terminals of the semiconductor chip are increased by a redistribution process, the size of the I/O terminals of the semiconductor chip and the interval between the I/O terminals of the semiconductor chip are not enough to directly mount the fan-in semiconductor package on the main board of the electronic device.

FIG. **5** is a schematic cross-sectional view illustrating a case in which a fan-in semiconductor package is mounted on an interposer substrate and is ultimately mounted on a main board of an electronic device.

FIG. **6** is a schematic cross-sectional view illustrating a case in which a fan-in semiconductor package is embedded in an interposer substrate and is ultimately mounted on a main board of an electronic device.

Referring to the drawings, in a fan-in semiconductor package **2200**, connection pads **2222**, that is, I/O terminals, of a semiconductor chip **2220** may be redistributed through an interposer substrate **2301**, and the fan-in semiconductor package **2200** may be ultimately mounted on a main board **2500** of an electronic device in a state of being mounted on the interposer substrate **2301**. In this case, solder balls **2270**, or the like, may be fixed by an underfill resin **2280**, or the like, and an external surface of the semiconductor chip **2220** may be covered with a molding material **2290**, or the like. Alternatively, a fan-in semiconductor package **2200** may be embedded in a separate interposer substrate **2302**, connec-

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tion pads **2222**, that is, I/O terminals, of the semiconductor chip **2220** may be redistributed by the interposer substrate **2302** in a state in which the fan-in semiconductor package **2200** is embedded in the interposer substrate **2302**, and the fan-in semiconductor package **2200** may be ultimately mounted on a main board **2500** of an electronic device.

As described above, it may be difficult to directly mount and use the fan-in semiconductor package on the main board of the electronic device. Therefore, the fan-in semiconductor package may be mounted on the separate interposer substrate and be then mounted on the main board of the electronic device through a packaging process or may be mounted and used on the main board of the electronic device in a state in which it is embedded in the interposer substrate. Fan-Out Semiconductor Package

FIG. 7 is a schematic cross-sectional view illustrating a fan-out semiconductor package.

Referring to the drawing, in a fan-out semiconductor package **2100**, for example, an external surface of a semiconductor chip **2120** may be protected by an encapsulant **2130**, and connection pads **2122** of the semiconductor chip **2120** may be redistributed outwardly of the semiconductor chip **2120** by an interconnection member **2140**. In this case, a passivation layer **2150** may further be formed on the interconnection member **2140**, and an under-bump metal layer **2160** may further be formed in openings of the passivation layer **2150**. Solder balls **2170** may further be formed on the under-bump metal layer **2160**. The semiconductor chip **2120** may be an integrated circuit (IC) including a body **2121**, the connection pads **2122**, a passivation layer, and the like. The interconnection member **2140** may include an insulating layer **2141**, redistribution layers **2142** formed on the insulating layer **2141**, and vias **2143** electrically connecting the connection pads **2122** and the redistribution layers **2142** to each other.

As described above, the fan-out semiconductor package may have a form in which I/O terminals of the semiconductor chip are redistributed and disposed outwardly of the semiconductor chip through the interconnection member formed on the semiconductor chip. As described above, in the fan-in semiconductor package, all I/O terminals of the semiconductor chip need to be disposed inside the semiconductor chip. Therefore, when a size of the semiconductor chip is reduced, a size and a pitch of balls need to be reduced, such that a standardized ball layout may not be used in the fan-in semiconductor package. On the other hand, the fan-out semiconductor package has the form in which the I/O terminals of the semiconductor chip are redistributed and disposed outwardly of the semiconductor chip through the interconnection member formed on the semiconductor chip as described above. Therefore, even in the case that a size of the semiconductor chip is reduced, a standardized ball layout may be used in the fan-out semiconductor package as it is, such that the fan-out semiconductor package may be mounted on the main board of the electronic device without using a separate interposer substrate, as described below.

FIG. 8 is a schematic cross-sectional view illustrating a case in which a fan-out semiconductor package is mounted on a main board of an electronic device.

Referring to the drawing, a fan-out semiconductor package **2100** may be mounted on a main board **2500** of an electronic device through solder balls **2170**, or the like. That is, as described above, the fan-out semiconductor package **2100** includes the interconnection member **2140** formed on the semiconductor chip **2120** and capable of redistributing the connection pads **2122** to a fan-out region outside of an

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area of the semiconductor chip **2120**, such that the standardized ball layout may be used in the fan-out semiconductor package **2100** as it is. As a result, the fan-out semiconductor package **2100** may be mounted on the main board **2500** of the electronic device without using a separate interposer substrate, or the like.

As described above, since the fan-out semiconductor package may be mounted on the main board of the electronic device without using the separate interposer substrate, the fan-out semiconductor package may be implemented to have a thickness lower than that of the fan-in semiconductor package using the interposer substrate. Therefore, the fan-out semiconductor package may be miniaturized and thinned. In addition, the fan-out semiconductor package has excellent thermal characteristics and electrical characteristics, such that it is particularly appropriate for a mobile product. Therefore, the fan-out semiconductor package may be implemented in a form more compact than that of a general package-on-package (POP) type semiconductor package using a printed circuit board (PCB), and may solve a problem occurring due to occurrence of a warpage phenomenon.

Meanwhile, the fan-out semiconductor package refers to package technology for mounting the semiconductor chip on the main board of the electronic device, or the like, as described above, and protecting the semiconductor chip from external impacts, and is conceptually different from a printed circuit board (PCB) such as an interposer substrate, or the like, having a scale, a purpose, and the like, different from those of the fan-out semiconductor package, and having the fan-in semiconductor package embedded therein.

A fan-out semiconductor package in which reliability of a via may be improved will be hereinafter described with reference to the drawings.

FIG. 9 is a schematic cross-sectional view illustrating an example of a fan-out semiconductor package.

FIG. 10 is a schematic plan view taken along line I-I' of the fan-out semiconductor package of FIG. 9.

FIG. 11A is a schematic enlarged view according to an example of A of the fan-out semiconductor package of FIG. 9.

FIG. 11B is a schematic enlarged view according to another example of A of the fan-out semiconductor package of FIG. 9.

FIG. 12 is a schematic enlarged view according to an example of B of the fan-out semiconductor package of FIG. 9.

Referring to the drawings, a fan-out semiconductor package **100A** according to an exemplary embodiment in the present disclosure may include a first interconnection member **110** having a through-hole **110H**, a semiconductor chip **120** disposed in the through-hole **110H** and having connection pads **122** disposed on one surface thereof, an encapsulant **130** encapsulating at least portions of the first interconnection member **110** and the semiconductor chip **120**, a second interconnection member **140** disposed on the first interconnection member **110** and one surface of the semiconductor chip **120** and redistributing the connection pads **122** up to a fan-out region, a passivation layer **150** disposed on one surface of the second interconnection member **140** and having openings **151** exposing at least portions of connection terminal pads of the second interconnection member **140**, an under-bump metal layer **160** disposed on the openings **151** of the passivation layer **150**, and connection terminals **170** disposed on the under-bump metal layer **160** and electrically connected to the connection pads **122** through the second interconnection member **140**.

In this case, at least one pair of connection pad **122-1** and connection terminal **170-1** of the connection pads **122** and the connection terminals **170** may be connected to each other by a first electrical pathway P-1 in the second interconnection member **140**, including a first via **143a-1** connected to the connection pad **122-1**, a first via pad **142a-1a** connected to the first via **143a-1**, a second via pad **142a-1b** disposed on the same layer as a layer on which the first via pad **142a-1a** is disposed and directly connected to the first via pad **142a-1a** or to the first via pad **142a-1a** through a wiring **142a-1c**, a second via **143b-1** connected to the second via pad **142a-1b**, a third via pad **142b-1a** connected to the second via **143b-1**, and a connection terminal pad **142b-1b** disposed on the same layer as a layer on which the third via pad **142b-1a** is disposed and directly connected to the third via pad **142b-1a**. The first and second via pads **142a-1a** and **142a-1b** may be disposed on a layer different from the layer on which the connection terminal pad **142b-1b** is disposed, and the third via pad **142b-1a** may be disposed on the same layer as the layer on which the connection terminal pad **142b-1b** is disposed. The first and second vias **143a-1** and **143b-1** may be disposed on layers different from each other.

The first via **143a-1** of the first electrical pathway P-1 may be disposed so that a central axis thereof is disposed in an inner region of the connection terminal pad **142b-1b** or an opening **151-1**. As described below, a distance between the central axis of the first via **143a-1** and a central axis of the connection terminal pad **142b-1b** may be within $\frac{1}{3}$ of a radius of the opening **151-1**. The second via **143b-1** may be disposed so that a central axis thereof is disposed in an outer region of the connection terminal pad **142b-1b** or the opening **151-1**.

The second and third via pads **142a-1b** and **142b-1a** connected to the second via **143b-1** may be disposed in the outer region of the opening **151-1**. Stress may be reduced through the first electrical pathway P-1, as described below. Therefore, the first electrical pathway P-1 may be formed in a region in which stress is severe as described below, such as a corner of a region in which the semiconductor chip **120** is disposed.

The connection terminal pad **142b-1b** may have a horizontal cross-sectional area wider than that of the third via pad **142b-1a** directly connected to the connection terminal pad **142b-1b**. Resultantly, a horizontal cross section of the connection terminal pad **142b-1b** and the third via pad **142b-1a** directly connected to each other may have, for example, a snowman shape. The horizontal cross section refers to a cross section in a plane in a direction perpendicular to a vertical direction of each component of the fan-out semiconductor package **100A** in the accompanying drawings. In this case, reliability may be further improved. In a case in which the first and second via pads **141a-1a** and **142a-1b** are directly connected to each other, a horizontal cross section of the first and second via pads **141a-1a** and **142a-1b** may have, for example, a snowman shape. Alternatively, in a case in which the first and second via pads **141a-1a** and **142a-1b** are connected to each other by the wiring **142a-1c**, a horizontal cross section of the first and second via pads **141a-1a** and **142a-1b** may have, for example, a dumbbell shape.

In addition, at least another pair of connection pad **122-2** and connection terminal **170-2** of the connection pads **122** and the connection terminals **170** may be connected to each other by a second electrical pathway P-2 in the second interconnection member **140**, including a third via **143a-2** connected to the connection pad **122-2**, a via pad **142a-2**

connected to the third via **143a-2**, a fourth via **143b-2** connected to the via pad **142a-2**, and a connection terminal pad **142b-2** connected to the fourth via **143b-2**. The via pad **142a-2** may be disposed on a layer different from layer on which the connection terminal pad **142b-2** is disposed. The third and fourth vias **143a-2** and **143b-2** may be disposed on layers different from each other.

The third and fourth vias **143a-2** and **143b-2** of the second electrical pathway P-2 may be disposed so that central axes thereof are disposed in an inner region of the connection terminal pad **142b-2** or an opening **151-2**. The central axes of the third and fourth vias **143a-2** and **143b-2** may be disposed to substantially coincide with that of the opening **151-2**. Here, the meaning of 'substantially' includes an error in a process.

The second electrical pathway P-2 may not reduce stress, but may significantly reduce a wiring distance. Therefore, the second electrical pathway P-2 may be formed in a region in which stress is not severe other than a region in which stress is severe as described below, such as an internal region, or the like, of the semiconductor chip **120**.

In general, in a case in which a fan-out semiconductor package is mounted directly on a main board, or the like, of an electronic device, reliability of connection terminals connecting the fan-out semiconductor package and the board to each other and vias in a second interconnection member connected to the connection terminals may be decreased due to stress generated owing to various causes. For example, warpages may be generated in the fan-out semiconductor package and the board due to a difference in a coefficient of thermal expansion (CTE) between a semiconductor chip and the main board. In this case, the warpage generated in the fan-out semiconductor package and the warpage generated in the board act in opposite directions, such that stress may be concentrated on the connection terminals connecting the fan-out semiconductor package and the board to each other, such as solder balls. This stress may cause a crack in the solder balls, and may be transferred into an interconnection member to generate delamination or a crack in vias in the interconnection member connected to connection pads of the semiconductor chip. In addition, the delamination of the vias in the interconnection member may also be generated due to heat generated when the semiconductor chip is turned on or off and stress generated when the semiconductor chip is cooled. As described above, temperature cycling reliability has been problematic.

On the other hand, in a case in which the vias **143a-1** and **143b-1** and the pads **142a-1a**, **142a-1b**, **142b-1a**, and **142b-1b** of the second interconnection member **140** are disposed so that stress may be reduced in a region in which the stress is concentrated as in the fan-out semiconductor package **100A** according to the exemplary embodiment, a reliability problem may be improved. In addition, the vias **143a-2** and **143b-2** may be disposed in a form different from the abovementioned form, such as a stacked via form, in a region in which stress is less concentrated, and effects such as reliability improvement, rapid signal transfer, and the like, may thus be accomplished.

The respective components included in the fan-out semiconductor package **100A** according to the exemplary embodiment will hereinafter be described below in more detail.

The first interconnection member **110** may support the fan-out semiconductor package **100A**. In addition, the first interconnection member **110** may allow uniformity of a thickness of the encapsulant **130** to be easily secured. In addition, the first interconnection member **110** may provide

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a routing region to form a redistribution layer, thereby reducing the number of layers of the second interconnection member 140. Resultantly, a defect occurring in a process of forming the second interconnection member 140 may be solved. The first interconnection member 110 may have the through-hole 110H. The through-hole 110H may have the semiconductor chip 120 disposed therein to be spaced apart from the first interconnection member 110 by a predetermined distance. That is, side surfaces of the semiconductor chip 120 may be surrounded by the first interconnection member 110. However, a form of the first interconnection member 110 is not limited thereto, but may be variously modified into other forms.

The first interconnection member 110 may include a first insulating layer 111a contacting the second interconnection member 140, a first redistribution layer 112a contacting the second interconnection member 140 and embedded in the first insulating layer 111a, a second redistribution layer 112b disposed on the other surface of the first insulating layer 111a opposing one surface of the first insulating layer 111a in which the first redistribution layer 112a is embedded, a second insulating layer 111b disposed on the first insulating layer 111a and covering the second redistribution layer 112b, and a third redistribution layer 112c disposed on the second insulating layer 111b. Since the first interconnection member 110 may include a large number of redistribution layers 112a, 112b, and 112c, the second interconnection member 140 may be further simplified. Therefore, a decrease in a yield depending on a defect occurring in a process of forming the second interconnection member 140 may be improved. Since the first redistribution layer 112a is embedded in the first insulating layer 111a, an insulating distance of an insulating layer 141a of the second interconnection member 140 may be relatively constant. The first redistribution layer 112a may be recessed in the first insulating layer 111a, such that a lower surface of the first insulating layer 111a may have a step with respect to a lower surface of the first redistribution layer 112a. Therefore, a phenomenon that a material of the encapsulant 130 is bled to the first redistribution layer 112a may be prevented. The first to third redistribution layers 112a, 112b, and 112c may be electrically connected to each other by first via layers (not illustrated) and second via layers 113b penetrating through the first and second insulating layers 111a and 111b.

Materials of the first and second insulating layers 111a and 111b are not particularly limited as long as the first and second insulating layers 111a and 111b may support the fan-out semiconductor package. For example, an insulating material may be used as materials of the first and second insulating layers 111a and 111b. In this case, a thermosetting resin such as an epoxy resin, a thermoplastic resin such as a polyimide resin, a resin having a reinforcement material such as a glass cloth or an inorganic filler impregnated in the thermosetting resin and the thermoplastic resin, such as prepreg, Ajinomoto Build up Film (ABF), FR-4, Bismaleimide Triazine (BT), or the like, may be used as the insulating material. Alternatively, a photoimageable dielectric (PID) resin may also be used as the insulating material.

The redistribution layers 112a, 112b, and 112c may serve to redistribute the connection pads 122 of the semiconductor chip 120, and a conductive material such as copper (Cu), aluminum (Al), silver (Ag), tin (Sn), gold (Au), nickel (Ni), lead (Pb), titanium (Ti), or alloys thereof, may be used as a material of each of the redistribution layers 112a, 112b, and 112c. The redistribution layers 112a, 112b, and 112c may have various functions depending on designs of layers corresponding thereto. For example, the redistribution layers

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112a, 112b and 112c may include ground (GND) patterns, power (PWR) patterns, signal (S) patterns, and the like. Here, the signal (S) patterns may include various signals except for the ground (GND) patterns, the power (PWR) patterns, and the like, such as data signals, and the like. In addition, the redistribution layers 112a, 112b, and 112c may include via pads, connection terminal pads, and the like. A surface treatment layer may further be formed on portions of the redistribution layer 112c exposed from the redistribution layers 112a, 112b, and 112c through openings formed in the encapsulant 130, if necessary. The surface treatment layer is not particularly limited as long as it is known in the related art, but may be formed by, for example, electrolytic gold plating, electroless gold plating, organic solderability preservative (OSP) or electroless tin plating, electroless silver plating, electroless nickel plating/substituted gold plating, direct immersion gold (DIG) plating, hot air solder leveling (HASL), or the like.

The first via layers (not illustrated) and the second via layers 113b may electrically connect the redistribution layers 112a and 112b formed on different layers to each other, resulting in an electrical pathway in the first interconnection member 110. A conductive material such as copper (Cu), aluminum (Al), silver (Ag), tin (Sn), gold (Au), nickel (Ni), lead (Pb), titanium (Ti), or alloys thereof, may be used as a material of each of the first via layers (not illustrated) and the second via layers 113b. Each of the first via layers (not illustrated) and the second via layers 113b may be entirely filled with the conductive material, or the conductive material may also be formed along a wall of respective via holes. In addition, each of the first via layers (not illustrated) and the second via layers 113b may have all shapes known in the related art, such as a tapered shape, a cylindrical shape, and the like.

The semiconductor chip 120 may be an integrated circuit (IC) provided in an amount of several hundreds to several millions of elements or more integrated in a single chip. The IC may be a known semiconductor chip, for example, an application processor (AP) such as a central processor (for example, a CPU), a graphic processor (for example, a GPU), a digital signal processor, a cryptographic processor, a microprocessor, a microcontroller, or the like. Alternatively, the IC may be a power management IC (PMIC). The AP and the PMIC, which are the semiconductor chip 120, may be disposed together with each other in the through-hole 110H of the first interconnection member 110. Alternatively, the AP and the PMIC may be integrated with each other as a single chip and be disposed in the through-hole 110H of the first interconnection member 110.

The semiconductor chip 120 may include a body 121, the connection pads 122 formed on one surface of the body 121, and a passivation layer 123 formed on the body 121 and covering portions of the connection pads 122. The body 121 may be formed on the basis of, for example, an active wafer. In this case, silicon (Si), germanium (Ge), gallium arsenide (GaAs), or the like, may be used as a basic material of the body 121. The connection pads 122 may electrically connect the semiconductor chip 120 to other components, and a conductive material such as aluminum (Al), or the like, may be used as a material of each of the connection pads 122. The connection pads 122 may be redistributed by the second interconnection member 140, the first interconnection member 110, and the like. A surface of the semiconductor chip 120 on which the connection pads 122 are formed may be an active surface, and an opposite surface of the semiconductor chip 120 to the active surface may be an inactive surface. The passivation layer 123 may serve to protect the body 121

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from external impact, and may be formed of, for example, an oxide film formed of SiO₂, etc., a nitride film formed of SiN, etc., or the like, or be formed of a double layer including an oxide film and a nitride film. In addition, an insulating layer, or the like, formed of SiO₂, etc., may be further disposed between the body 121 and the connection pads 122 or between the body 121 and the passivation layer 123.

The lower surface of the first redistribution layer 112a of the first interconnection member 110 may be disposed on a level above a lower surface of the connection pad 122 of the semiconductor chip 120. In addition, a distance between a redistribution layer 142a of the second interconnection member 140 and the first redistribution layer 112a of the first interconnection member 110 may be greater than that between the redistribution layer 142a of the second interconnection member 140 and the connection pad 122 of the semiconductor chip 120. Here, the first redistribution layer 112a may be recessed in the first insulating layer 111a. The second redistribution layer 112b of the first interconnection member 110 may be disposed on a level between the active surface and the inactive surface of the semiconductor chip 120. The first interconnection member 110 may be formed to a thickness corresponding to that of the semiconductor chip 120. Therefore, the second redistribution layer 112b formed in the first interconnection member 110 may be disposed on a level between the active surface and the inactive surface of the semiconductor chip 120.

The encapsulant 130 may be configured to protect the first interconnection member 110 or the semiconductor chip 120. An encapsulation form of the encapsulant 130 is not particularly limited, but may be a form in which the encapsulant 130 surrounds at least portions of the first interconnection member 110 or the semiconductor chip 120. For example, the encapsulant 130 may fill the first interconnection member 110, the other surface of the semiconductor chip 120, and a space between the first interconnection member 110 and the semiconductor chip 120 within the through-hole 110H. In addition, the encapsulant 130 may also fill at least a portion of a space between the passivation layer 123 of the semiconductor chip 120 and the second interconnection member 140. Meanwhile, the encapsulant 130 may fill the through-hole 110H to thus serve as an adhesive and reduce buckling of the semiconductor chip 120 depending on materials of the encapsulant 130. Openings opening at least portions of the second redistribution layer 112b formed on the other surface of the first interconnection member 110 may be formed in the encapsulant 130. The opened portions of the second redistribution layer 112b may be utilized as marking patterns. Alternatively, separate connection terminals, or the like, may be connected to the opened portions of the second redistribution layer 112b to thus be applied to a package-on-package structure, and a surface mount technology (SMT) component may be disposed on the opened portions of the second redistribution layer 112b.

The materials of the encapsulant 130 are not particularly limited, but may be, for example, an insulating material. In more detail, for example, ABF, or the like, that includes an inorganic filler and an insulating resin, but does not include a glass cloth may be used as a material of the encapsulant 130. In this case, a void problem or a delamination problem may be solved. Meanwhile, the inorganic filler may be a known inorganic filler, and the insulating resin may be a known epoxy resin, or the like. However, the inorganic filler and the insulating resin are not limited thereto.

The second interconnection member 140 may be configured to redistribute the connection pads 122 of the semi-

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conductor chip 120. Several tens to several hundreds of connection pads 122 having various functions may be redistributed by the second interconnection member 140, and may be physically or electrically connected to an external source through connection terminals 170 to be described below depending on the functions. The second interconnection member 140 may include insulating layers 141a and 141b, redistribution layers 142a and 142b, and via layers 143a and 143b.

An insulating material may be used as a material of each of the insulating layers 141a and 141b. In this case, a photosensitive insulating material such as a photoimageable dielectric (PID) resin may also be used as the insulating material. In this case, each of the insulating layers 141a and 141b may be formed to have a smaller thickness, and a fine pitch of each of vias of the first via layers 143a and the second via layers 143b may be achieved more easily. Materials of the insulating layers 141a and 141b may be the same as each other or may be different from each other, if necessary. The insulating layers 141a and 141b may be integrated with each other depending on processes, so that a boundary therebetween may not be readily apparent.

The redistribution layers 142a and 142b may substantially serve to redistribute the connection pads 122, and a conductive material such as copper (Cu), aluminum (Al), silver (Ag), tin (Sn), gold (Au), nickel (Ni), lead (Pb), titanium (Ti), or alloys thereof, may be used as a material of each of the redistribution layers 142a and 142b. The redistribution layers 142a and 142b may have various functions depending on designs of layers corresponding thereto. For example, the redistribution layers 142a and 142b may include ground (GND) patterns, power (PWR) patterns, signal (S) patterns, and the like. Here, the signal (S) patterns may include various signals except for the ground (GND) patterns, the power (PWR) patterns, and the like, such as data signals, and the like. In addition, the redistribution layers 142a and 142b may include via pads, connection terminal pads, and the like. A surface treatment layer (not illustrated) may further be formed on portions of a redistribution layer exposed from the redistribution layers 142a and 142b, if necessary. The surface treatment layer is not particularly limited as long as it is known in the related art, and may be formed by, for example, electrolytic gold plating, electroless gold plating, OSP or electroless tin plating, electroless silver plating, electroless nickel plating/substituted gold plating, DIG plating, HASL, or the like.

The via layers 143a and 143b may electrically connect the redistribution layers 142a and 142b, the connection pads 122, or the like, formed on different layers to each other, resulting in an electrical pathway in the fan-out semiconductor package 100A. A conductive material such as copper (Cu), aluminum (Al), silver (Ag), tin (Sn), gold (Au), nickel (Ni), lead (Pb), titanium (Ti), or alloys thereof, may be used as a material of each of the via layers 143a and 143b. Each of the via layers 143a and 143b may be entirely filled with the conductive material, or the conductive material may also be formed along a wall of each of vias unlike illustrated in the drawing. In addition, each of the via layers 143a and 143b may have all shapes known in the related art, such as a tapered shape, a cylindrical shape, and the like.

Thicknesses of the redistribution layers 112a, 112b, and 112c of the first interconnection member 110 may be greater than those of the redistribution layers 142a and 142b of the second interconnection member 140. Since the first interconnection member 110 may have a thickness equal to or greater than that of the semiconductor chip 120, the redistribution layers 112a, 112b, and 112c may be formed to be

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large depending on a scale of the first interconnection member **110**. On the other hand, the redistribution layers **142a** and **142b** of the second interconnection member **140** may be formed to be relatively small for thinness.

The passivation layer **150** may be additionally configured to protect the second interconnection member **140** from external physical or chemical damage. The passivation layer **150** may have the openings **151** exposing at least portions of any one of the redistribution layers **142a** and **142b** of the second interconnection member **140**. The openings **151** may expose the entirety or only a portion of a surface of the redistribution layer **142b**, and may also expose side surfaces of the redistribution layer **142b** in some cases. In a case in which the passivation layer **150** is not formed and the second interconnection member **140** has a plurality of insulating layers, the openings **151** may be formed in the outermost insulating layer of the plurality of insulating layers. The respective openings **151** may also be formed of a plurality of vias in some cases.

A material of the passivation layer **150** is not particularly limited, but may be a photosensitive insulating material such as a PID resin. Alternatively, a solder resist may also be used as a material of the passivation layer **150**. Alternatively, an insulating resin that does not include a glass cloth, but has a filler impregnated therein, such as ABF including an inorganic filler and an epoxy resin, or the like, may be used as the material of the passivation layer **150**. In a case in which the ABF, or the like, is used as the material of the passivation layer **150**, a material satisfying Equations 1 to 4 may be easily selected. In this case, board level reliability of the electronic component package may be improved.

$$\text{Elastic Modulus} \times \text{Coefficient of Thermal Expansion} \leq 230 \text{ GPa} \cdot \text{ppm}/^\circ \text{C.} \quad \text{Equation 1:}$$

$$\text{Thickness} \geq 10 \text{ } \mu\text{m} \quad \text{Equation 2:}$$

$$\text{Surface Roughness} \geq 1 \text{ nm} \quad \text{Equation 3:}$$

$$\text{Moisture Absorption Ratio} \leq 1.5\% \quad \text{Equation 4:}$$

The under-bump metal layer **160** may be additionally configured to improve connection reliability of connection terminals **170** to be described below and improve board level reliability of the fan-out semiconductor package **100A**. The under-bump metal layer **160** may be disposed on walls in the openings **151** of the passivation layer **150** and the exposed redistribution layer **142b** of the second interconnection member **140**. The under-bump metal layer **160** may be formed by a metallization method using a known metal.

The connection terminals **170** may be configured to physically or electrically externally connect the fan-out semiconductor package **100A**. For example, the fan-out semiconductor package **100A** may be mounted on the main board of the electronic device through the connection terminals **170**. Each of the connection terminals **170** may be formed of a conductive material such as a solder, or the like. However, this is only an example, and a material of each of the connection terminals **170** is not limited thereto. Each of the connection terminals **170** may be a land, a ball, a pin, or the like. The connection terminal **170** may be formed of multiple layers or a single layer. When the connection terminals **170** are formed of the multiple layers, the connection terminals **170** may include a copper pillar and a solder. When the connection terminals **170** are formed of the single layer, the connection terminals **170** may include a tin-silver solder or copper. However, this is only an example, and the connection terminals **170** are not limited thereto. The number, interval, dispositional form, or the like, of the

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connection terminals **170** is not particularly limited, and may be sufficiently modified by a person skilled in the art depending on design particulars. For example, the connection terminals **170** may be provided in an amount of several tens to several thousands according to the number of connection pads **122** of the semiconductor chip **120**, but are not limited thereto, and may also be provided in an amount of several tens to several thousands or more or several tens to several thousands or less.

At least one of the connection terminals **170** may be disposed in a fan-out region. The fan-out region is a region except for the region in which the semiconductor chip **120** is disposed. That is, the fan-out semiconductor package **100A** according to the exemplary embodiment may be a fan-out package. The fan-out package may have excellent reliability as compared to a fan-in package, may implement a plurality of input/output (I/O) terminals, and may facilitate a 3D interconnection. In addition, as compared to a ball grid array (BGA) package, a land grid array (LGA) package, or the like, the fan-out package may be mounted on an electronic device without a separate board. Thus, the fan-out package may be manufactured to have a reduced thickness, and may have price competitiveness.

Although not illustrated in the drawings, a metal layer may be further disposed on an inner wall of the through-hole **110H** of the first interconnection member **110**, if necessary. That is, the side surfaces of the semiconductor chip **120** may also be surrounded by the metal layer. Heat generated from the semiconductor chip **120** may be effectively radiated in an upward or downward direction of the fan-out semiconductor package **100A** through the metal layer, and electromagnetic waves may be effectively blocked by the metal layer. If necessary, a plurality of semiconductor chips may be disposed in the through-hole **110H** of the first interconnection member **110**, and the number of through-holes **110H** of the first interconnection member **110** may be plural and semiconductor chips may be disposed in the through-holes, respectively. In addition, separate passive components such as a condenser, an inductor, and the like, may be disposed together with the semiconductor chip in the through-hole **110H**. In addition, a surface mount technology (SMT) component may be mounted on the passivation layer **150**.

FIG. 13 is a schematic cross-sectional view illustrating another example of a fan-out semiconductor package.

Referring to the drawing, in a fan-out semiconductor package **100B** according to another exemplary embodiment in the present disclosure, a first interconnection member **110** may include a first insulating layer **111a**, a first redistribution layer **112a** and a second redistribution layer **112b** disposed on both surfaces of the first insulating layer **111a**, respectively, a second insulating layer **111b** disposed on the first insulating layer **111a** and covering the first redistribution layer **112a**, a third redistribution layer **112c** disposed on the second insulating layer **111b**, a third insulating layer **111c** disposed on the first insulating layer **111a** and covering the second redistribution layer **112b**, and a fourth redistribution layer **112d** disposed on the third insulating layer **111c**. The first to fourth redistribution layers **112a**, **112b**, **112c**, and **112d** may be electrically connected to each other by first to third via layers (not illustrated) penetrating through the first to third insulating layers **111a**, **111b**, and **111c**.

The first insulating layer **111a** may have a thickness greater than those of the second insulating layer **111b** and the third insulating layer **111c**. The first insulating layer **111a** may basically be relatively thick in order to maintain rigidity, and the second and third insulating layers **111b** and **111c** may be disposed in order to form a larger number of

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redistribution layers **112c** and **112d**. The first insulating layer **111a** may include an insulating material different from those of the second insulating layer **111b** and the third insulating layer **111c**. For example, the first insulating layer **111a** may be, for example, prepreg including a glass cloth, an inorganic filler, and an insulating resin, and the second insulating layer **111b** and the third insulating layer **111c** may be an ABF or a photosensitive insulating film including an inorganic filler and an insulating resin. However, the materials of the first insulating layer **111a** and the second and third insulating layers **111b** and **111c** are not limited thereto.

A lower surface of the third redistribution layer **112c** of the first interconnection member **110** may be disposed on a level below a lower surface of the connection pad **122** of the semiconductor chip **120**. In addition, a distance between a redistribution layer **142a** of the second interconnection member **140** and the third redistribution layer **112c** of the first interconnection member **110** may be smaller than that between the redistribution layer **142a** of the second interconnection member **140** and the connection pads **122** of the semiconductor chip **120**. Here, the third redistribution layer **112c** may be disposed on the second insulating layer **111b** in protruding form, resulting in contacting the second interconnection member **140**.

The first redistribution layer **112a** and the second redistribution layer **112b** of the first interconnection member **110** may be disposed on a level between an active surface and an inactive surface of the semiconductor chip **120**. The first interconnection member **110** may be formed to a thickness corresponding to that of the semiconductor chip **120**. Therefore, the first redistribution layer **112a** and the second redistribution layer **112b** formed in the first interconnection member **110** may be disposed on a level between the active surface and the inactive surface of the semiconductor chip **120**.

Thicknesses of the redistribution layers **112a**, **112b**, **112c**, and **112d** of the first interconnection member **110** may be greater than those of the redistribution layers **142a** and **142b** of the second interconnection member **140**. Since the first interconnection member **110** may have a thickness equal to or greater than that of the semiconductor chip **120**, the redistribution layers **112a**, **112b**, **112c**, and **112d** may also be formed to be large. On the other hand, the redistribution layers **142a** and **142b** of the second interconnection member **140** may be formed to be relatively small for thinness.

A description, or the like, of configurations other than the abovementioned configuration, such as a description of a first electrical pathway P-1 and a second electrical pathway P-2, a description of region A and region B, or the like, may overlap the description provided above, and is thus omitted.

FIG. 14 is a schematic view illustrating a stress reducing effect in a case in which a central axis of a via is disposed in an outer region of a connection terminal pad or an opening.

Referring to the drawing, it may be appropriated that a stress reducing effect is significantly larger in a case in which a via **143b-1** in the second interconnection member **140** is disposed so that a central axis thereof is formed in an outer region of a connection terminal pad **142b-1b** or an opening **151-1** as in the fan-out semiconductor package **100A** according to the exemplary embodiment than in a case in which a via **143b-2** is disposed so that a central axis thereof substantially coincides with that of a connection terminal pad **142b-1b** or an opening **151-1**.

FIGS. 15A and 15B are schematic views illustrating relative magnitudes of stress applied to vias at positions within a fan-out semiconductor package.

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Referring to the drawings, the second interconnection member **140** may include a fan-in region R1 corresponding to a region in which the semiconductor chip **120** is disposed and a fan-out region R2 surrounding the fan-in region R1. In this case, it may be appreciated that stress applied to vias in the second interconnection member is significantly increased in an outward direction in the fan-in region R1. For example, the stress may be severe particularly in four corner portions of the fan-in region R1. Therefore, the first electrical pathways P-1 that may reduce the stress as described above may be designed in at least the corner portions of the fan-in region R1. Similarly, stress applied to vias in the second interconnection member may be significantly increased in an outward direction in the fan-out region R2. Therefore, electrical pathways that may reduce the stress as described above may also be designed in at least corner portions of the fan-out region R2, but are not limited thereto. The second electrical pathways P-2 that may significantly reduce a wiring distance may be designed in a region in which stress is not severe, such as an internal region of the fan-in region R1, or the like.

FIG. 16 is a schematic view illustrating stress depending on a distance between a central axis of a via connected to a connection pad of a semiconductor chip and a central axis of a connection terminal pad or an opening.

Referring to the drawing, it may be appreciated that in a case in which first and second vias **143a-1** and **143b-1** are disposed so that central axes thereof are misaligned with each other as in the fan-out semiconductor package **100A** according to the exemplary embodiment, a stress reducing effect may be increased as misalignment between the central axis of the first via **143a-1** positioned at an upper portion in the drawing and a central axis of the connection terminal pad **142b-1b** or the opening **151-1** is reduced. For example, it may be appreciated that in a case in which a distance between the central axis of the first via **143a-1** and the central axis of the connection terminal pad **142b-1b** or the opening **151-1** is within $\frac{1}{3}$ of a radius of the opening **151-1**, a stress level of 120% or less may be maintained.

As set forth above, according to the exemplary embodiment in the present disclosure, a fan-out semiconductor package in which reliability of a via may be improved may be provided.

While exemplary embodiments have been shown and described above, it will be apparent to those skilled in the art that modifications and variations could be made without departing from the scope of the present invention as defined by the appended claims.

What is claimed is:

1. A fan-out semiconductor package comprising:
 - a semiconductor chip comprising:
 - an active surface comprising a connection pad disposed on the active surface of the semiconductor chip; and
 - an inactive surface opposing the active surface;
 - an encapsulant encapsulating at least a portion of the semiconductor chip;
 - a first conductive structure comprising:
 - a first via adjacent to the semiconductor chip in a first direction; and
 - a first via pad connected to the first via;
 - a second conductive structure comprising:
 - a second via spaced apart from the first via in a second direction perpendicular to the first direction;
 - a second via pad extended from the second via in the second direction;
 - a third via connected to the second via pad; and

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a third via pad extended from the third via in the second direction; and
 wherein the second via comprises a first central axis and the third via comprises a second central axis, the first central axis and the second central axis being displaced in the second direction,
 wherein the second conductive structure is disposed farther from a central axis of the semiconductor chip than the first conductive structure,
 wherein the first via comprises a third central axis, and the first via pad comprises a fourth central axis, and
 wherein the first via and the first via pad are disposed such that the third central axis and the fourth central axis substantially coincide with each other.

2. The fan-out semiconductor package of claim 1, wherein the second conductive structure is located in a fan-out region, and

the fan-out region does not overlap the semiconductor chip in the first direction.

3. The fan-out semiconductor package of claim 1, wherein the first conductive structure is located in a fan-in region, and

the fan-in region overlaps the semiconductor chip in the first direction.

4. The fan-out semiconductor package of claim 1, wherein the connection pad comprises a fifth central axis, and the first via and the first via pad are disposed such that the third central axis and the fourth central axis substantially coincide with the fifth central axis.

5. The fan-out semiconductor package of claim 1, wherein the fan-out semiconductor package further comprises a first insulating layer having a first via hole in which the second via is disposed, and a second insulating layer having a second via hole in which the third via is disposed,

wherein the first insulating layer being disposed below the active surface of the semiconductor chip, and
 wherein the second insulating layer being disposed below the first insulating layer.

6. The fan-out semiconductor package of claim 5, wherein the second and third vias have a shape in which a conductive material is formed along a wall of respective the first and second via holes.

7. The fan-out semiconductor package of claim 5, wherein the second insulating layer covers the second via and the second via pad.

8. The fan-out semiconductor package of claim 1, wherein the first via is connected to the connection pad.

9. A fan-out semiconductor package comprising:
 a semiconductor chip comprising a connection pad being disposed at a first level;

an encapsulant encapsulating at least a portion of the semiconductor chip;

a first conductive structure comprising:

a first via pad structure disposed at a second level lower than the first level;

a first via connected to the first via pad structure;

a second via pad structure disposed at a third level lower than the second level; and

a second via connected to the first via pad structure, and the second via pad structure;

a second conductive structure comprising:

a third via pad structure disposed below the connection pad; and

a third via connected to the connection pad and the third via pad structure,

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wherein the first via comprises a first central axis and the second via comprises a second central axis, the first central axis and the second central axis being displaced in plan view,

wherein the third via pad structure comprises a third via pad connected to the third via, the third via pad being disposed below the connection pad,

wherein the second conductive structure further comprises a fourth via pad disposed below the third via pad, and a fourth via connected to the third via pad and the fourth via pad,

wherein the third via pad comprises a third central axis, the third via comprises a fourth central axis, the fourth via pad comprises a fifth central axis, and the fourth via comprises a sixth central axis, and

wherein the third via pad, the third via, the fourth via pad, and the fourth via are disposed such that the third central axis, the fourth central axis, the fifth central axis, and the sixth central axis substantially coincide with each other.

10. The fan-out semiconductor package of claim 9, wherein the first via pad structure comprises a first via pad extended from an edge of the first via in a horizontal direction, and

wherein the second via pad structure comprises a second via pad extended from an edge of the second via in the horizontal direction.

11. The fan-out semiconductor package of claim 10, wherein the second via pad overlaps the first via in a vertical direction.

12. The fan-out semiconductor package of claim 10, wherein the first central axis disposed within a first inner region of the second via pad and the second central axis disposed out of the first inner region of the second via pad.

13. The fan-out semiconductor package of claim 9, wherein the first via pad structure comprises:

a first pad connected to the first via; and

a second pad connected to the second via and the first pad, and coplanar with first pad,

wherein the second via pad structure comprises:

a third pad connected to the second via; and

a fourth pad connected to the third pad and coplanar with the third pad.

14. The fan-out semiconductor package of claim 13, wherein the first central axis disposed within a first inner region of the fourth pad and the second central axis disposed out of the first inner region of the fourth pad.

15. The fan-out semiconductor package of claim 9, wherein the third via pad overlaps the connection pad in a vertical direction.

16. The fan-out semiconductor package of claim 9, wherein the third via comprises a third central axis and the fourth via comprises a fourth central axis, the third central axis and the fourth central axis being disposed within a second inner region of the fourth via pad.

17. A fan-out semiconductor package comprising:

a semiconductor chip comprising a connection pad;

an encapsulant encapsulating at least a portion of the semiconductor chip;

a first conductive structure comprising:

a first via pad structure disposed adjacent to the semiconductor chip in a first direction; and

a first via connected to the connection pad of the semiconductor chip and the first via pad structure; and

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a second conductive structure comprising:
a second via pad structure spaced apart from the first
via pad structure of the first conductive structure in
a second direction perpendicular to the first direc-
tion; 5
a second via connected to the second via pad structure;
a third via pad structure disposed below the second via
pad structure; and
a third via connected to the second via pad structure and
the third via pad structure, 10
wherein the second via comprises a first central axis and
the third via comprises a second central axis, the first
central axis and the second central axis being displaced
in the second direction, and
wherein the second conductive structure is disposed far- 15
ther from a central axis of the semiconductor chip than
the first conductive structure in the second direction,
wherein the first via comprises a third central axis, and the
first via pad structure comprises a fourth central axis,
and 20
wherein the first via and the first via pad structure are
disposed such that the third central axis and the fourth
central axis substantially coincide with each other.

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